

## SEMICONDUCTOR TECHNICAL DATA

## KTA1664

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH CURRENT APPLICATION.

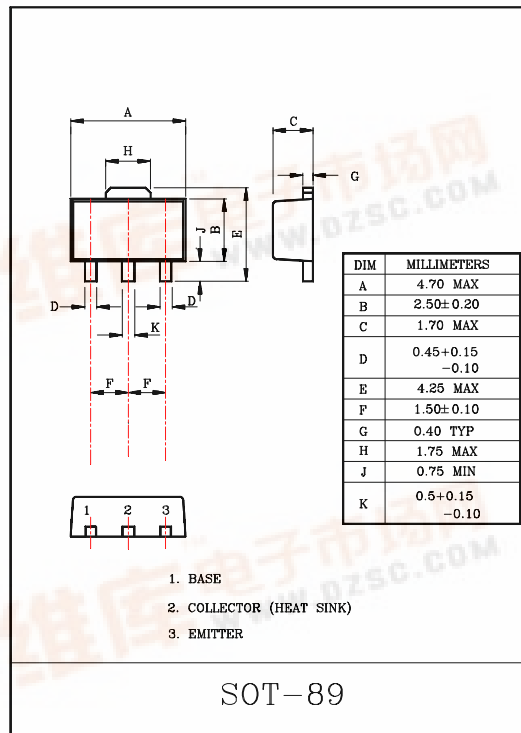
### FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4376.

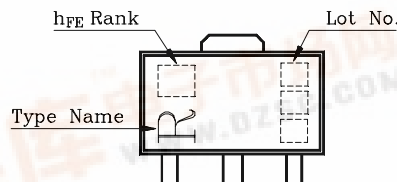
### MAXIMUM RATINGS(Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-35	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-800	mA
Base Current	$I_B$	-160	mA
Collector Power Dissipation	$P_C$	500	mW
	$P_{C^*}$	1	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

$P_{C^*}$ :KTA1664 mounted on ceramic substrate(250mm<sup>2</sup>x0.8t)



### Marking



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-35V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-1V, I_C=-100mA$	100	-	320	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$	-	-	-0.7	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-10mA$	-0.5	-	-0.8	V
Transition Frequency	$f_T$	$V_{CE}=-5V, I_C=-10mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$	-	19	-	pF

Note :  $h_{FE(1)}$  Classification O:100~200 , Y:160~320



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